



YJB118G08H

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	85V
I_D	118A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	6 mohm
$R_{DS(ON)}$ (at $V_{GS}=6V$)	9 mohm
100% UIS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$

Applications

Battery management
control and drive
UPS (Uninterruptible Power Supplies)

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit
Drain-source Voltage		V_{DS}	85
Gate-source Voltage		V_{GS}	± 20
Drain Current	$T_C=25^\circ C$	I_D	118
	$T_C=100$		74.6
Pulsed Drain Current ^A		I_{DM}	472



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Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250	85	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V, V _{GS} =0V	-	-	1	
		V _{DS} =85V, V _{GS} =0V, T _J =150	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ± 20V, V _{DS} =0V	-	-	± 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250	2	3	4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =59A	-	4.5	6	m
		V _{GS} =10V, I _D =20A	-	4.5	6	
		V _{GS} =6V, I _D =20A	-	7	9	
Diode Forward Voltage	V _{SD}	I _S =59A, V _{GS} =0V	-	0.9	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	1.8	-	
Maximum Body-Diode Continuous Current	I _S		-	-	118	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	-	4400	-	pF
Output Capacitance	C _{oss}		-	1650	-	
Reverse Transfer Capacitance	C _{rss}		-	150	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =40V, I _D =59A	-	63	-	nC
Gate-Source Charge	Q _{gs}		-	20	-	
Gate-Drain Charge	Q _{gd}		-	22	-	
Reverse Recovery Charge	Q _{rr}	I _F =59A, di/dt=300A/us	-	85	-	nC
Reverse Recovery Time	t _{rr}		-	33	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =40V, I _D =59A R _{GEN} =2.2	-	20	-	ns
Turn-on Rise Time	t _r		-	100	-	
Turn-off Delay Time	t _{D(off)}		-	24	-	
Turn-off fall Time	t _f		-	7	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25, V_{DD}=50V, V_G=10V, R_G 0.5mH, I_{AS}=39A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_θ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25. The maximum allowed junction temperature of 150. The value in any given application depends on the user's specific board design.



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Typical Electrical and Thermal Characteristics Diagrams

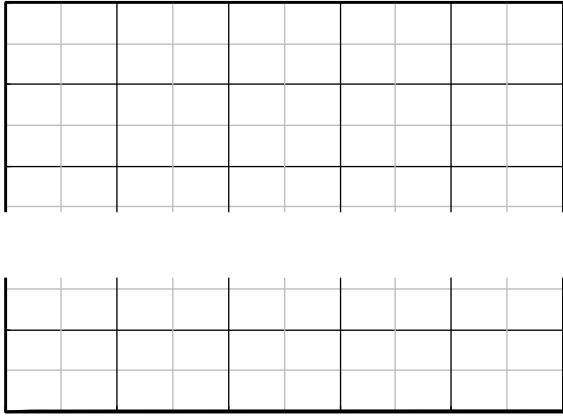


Figure1. Output Characteristics

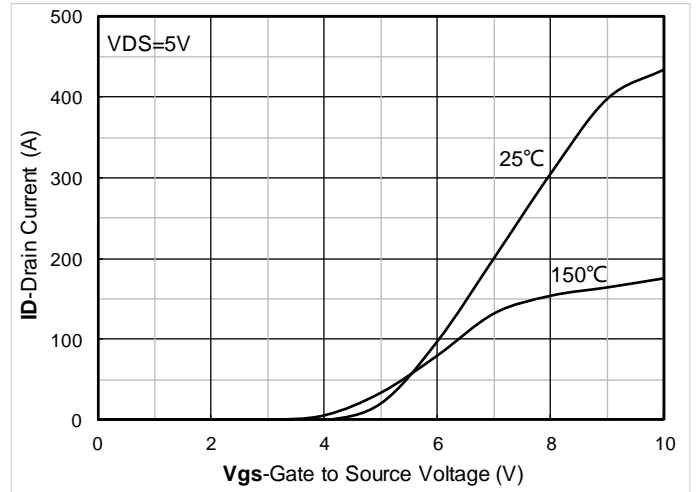


Figure2. Transfer Characteristics

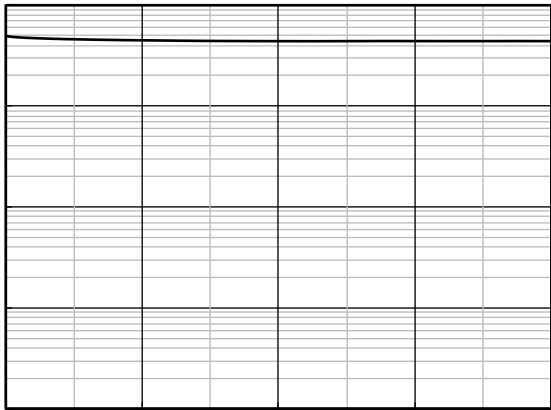


Figure3. Capacitance Characteristics

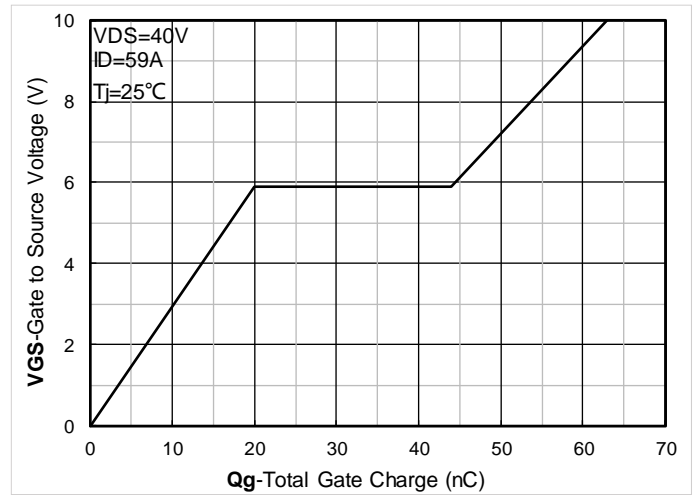


Figure4. Gate Charge

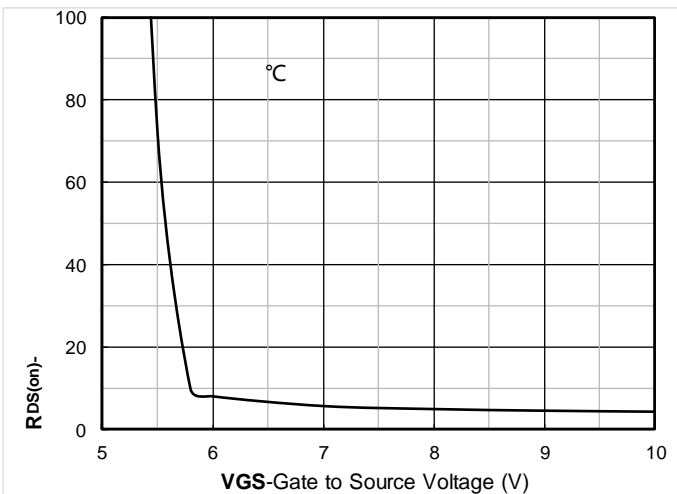


Figure5. On-Resistance vs Gate to Source Voltage

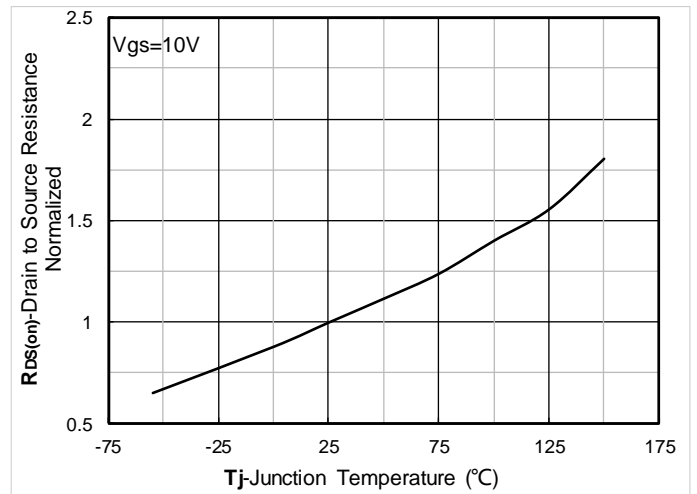


Figure6. Normalized On-Resistance



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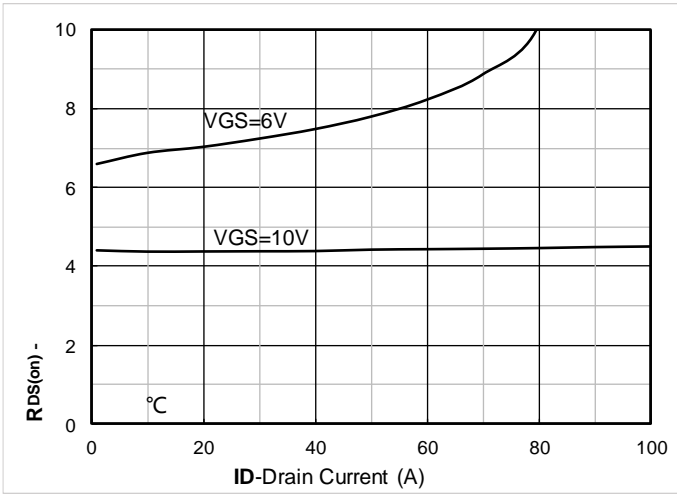


Figure7. RDS(on) VS Drain Current

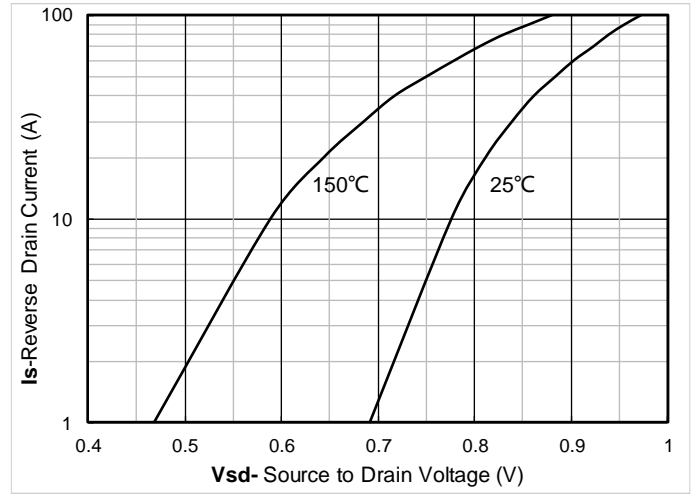


Figure8. Forward characteristics of reverse diode

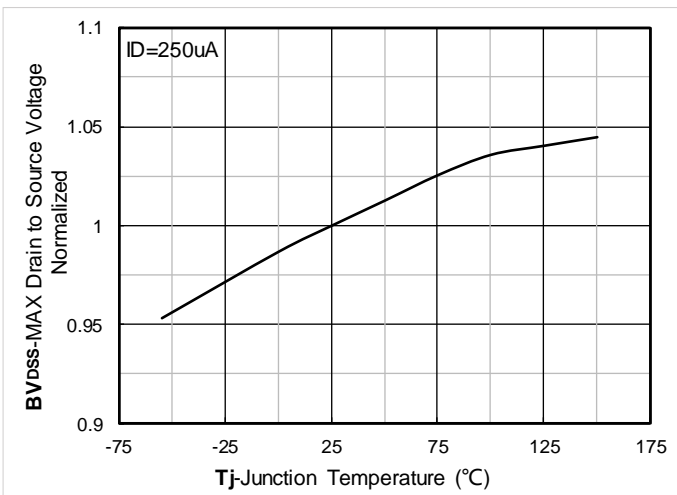


Figure9. Normalized breakdown voltage

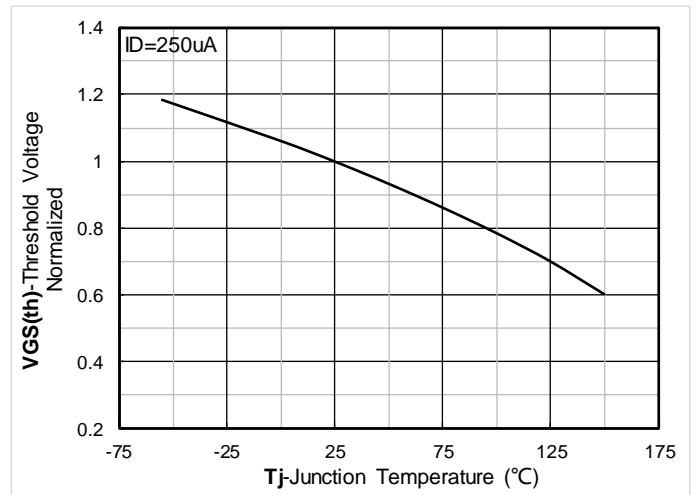


Figure10. Normalized Threshold voltage

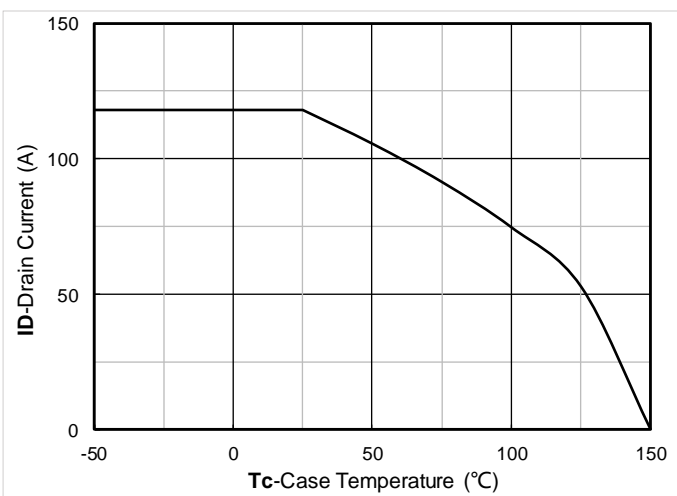


Figure11. Current dissipation

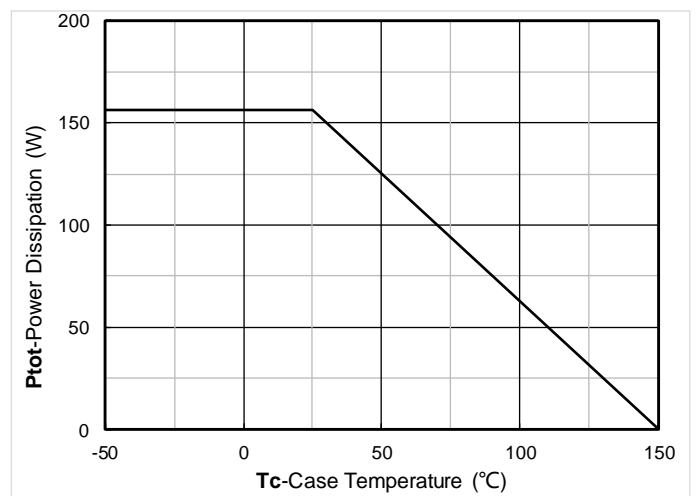


Figure12. Power dissipation

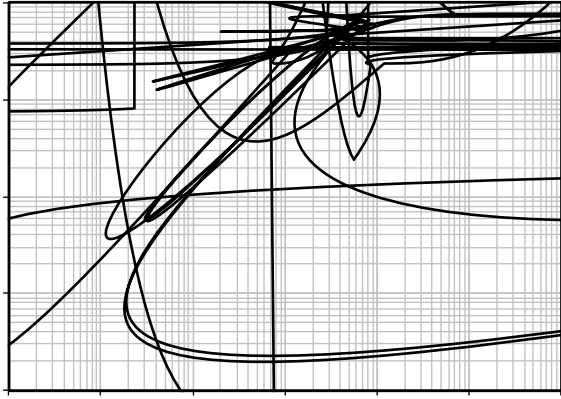


Figure13. Maximum Transient Thermal Impedance

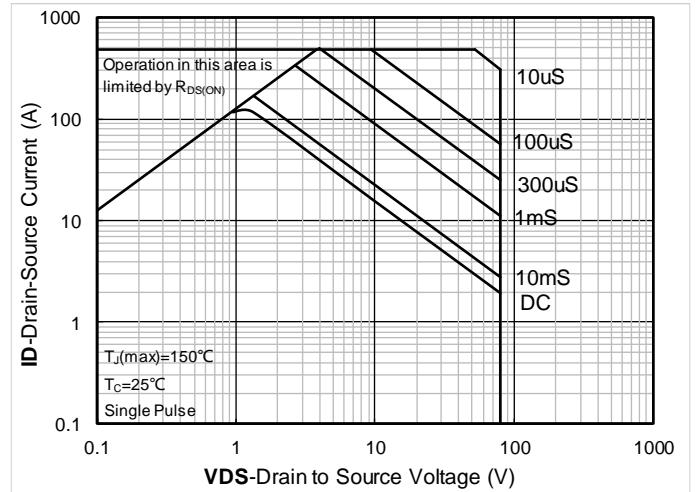
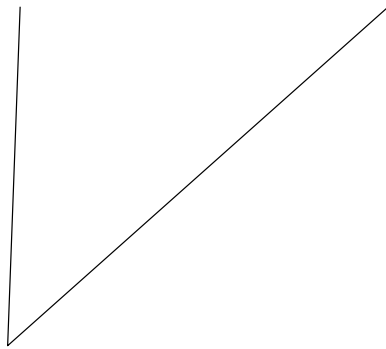


Figure14. Safe Operation Area

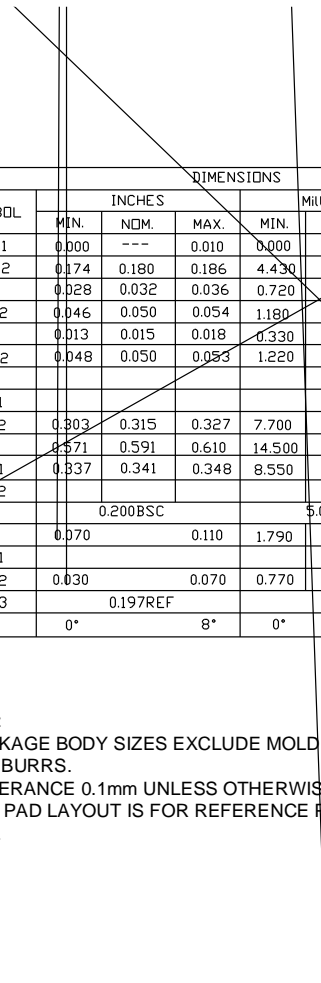


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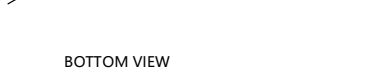
TO-263-HY Package information



TOP VIEW



SIDE VIEW



BOTTOM VIEW

SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.340	1.460
D1						
D2	0.303	0.315	0.327	7.700		8.300
E	0.571	0.591	0.610	14.500		15.500
E1	0.337	0.341	0.348	8.550		8.850
E2						
e		0.200BSC			5.080BSC	
L	0.070		0.110	1.790		2.790
L1						
L2	0.030		0.070	0.770		1.770
L3		0.197REF				
			8°			8°

NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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